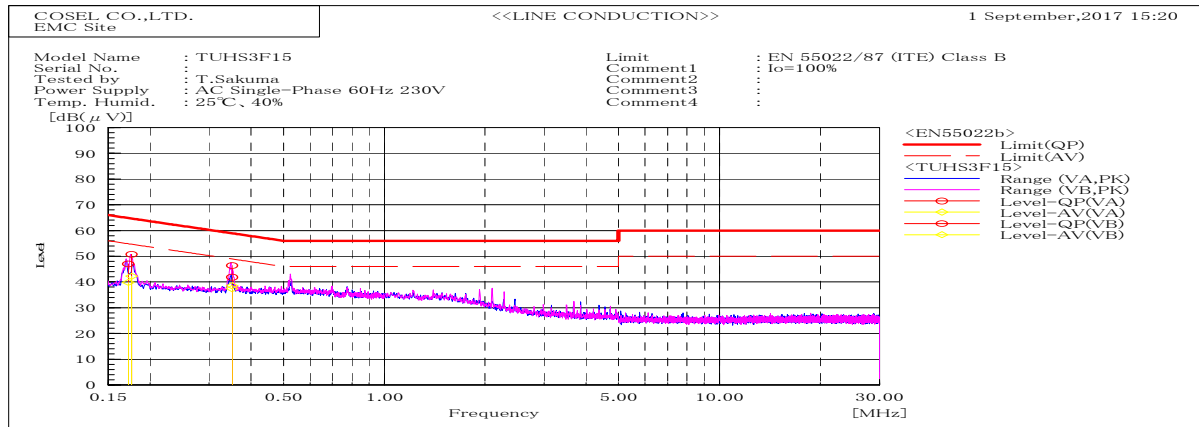
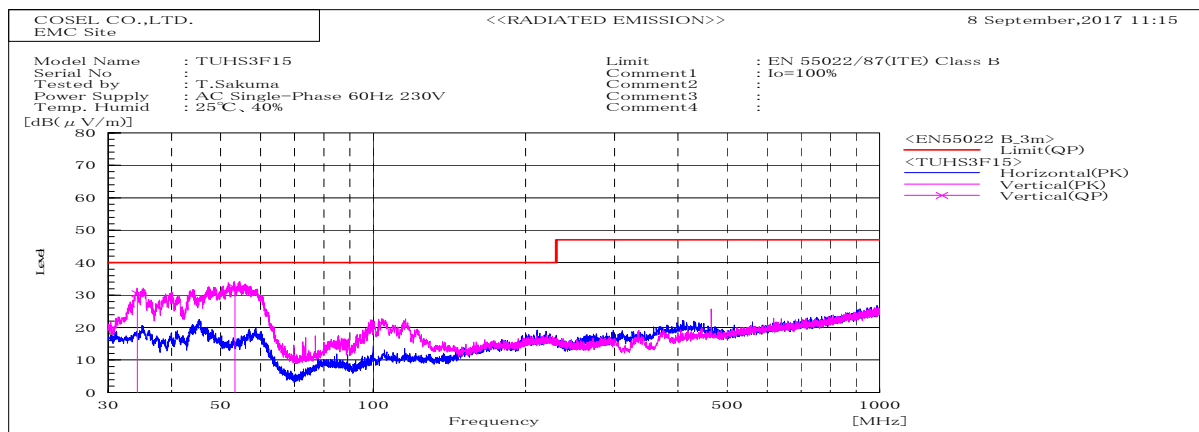


DATA SHEET		Date	13-Sep-17
Model	TUHS3F15	Temp.	25 degreeC
Test	EMI Line conduction & Radiated emission	Humid.	40 %RH
		Tested by	T.Sakuma



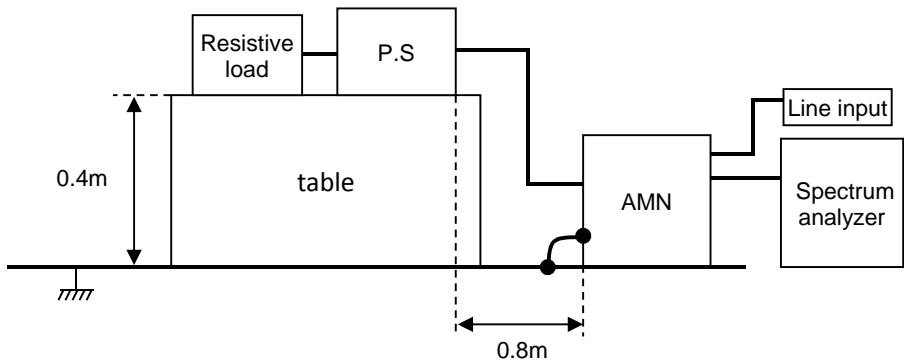
Frequency MHz	Harm	Line Phase	Reading dB(μV)		Factor dB	Level dB(μV/m)		Limit dB(μV/m)		Margin dB		Pass/Fail	Remark
			QP	AV		QP	AV	QP	AV	QP	AV		
0.17221		VA	26.0	18.8	21.0	47.0	39.8	64.9	54.9	17.9	15.1	Pass	
0.17592		VB	29.7	21.2	21.0	50.7	42.2	64.7	54.7	14.0	12.5	Pass	
0.35119		VB	25.5	17.6	20.9	46.4	38.5	58.9	48.9	12.5	10.4	Pass	
0.35174		VA	20.9	16.5	20.9	41.8	37.4	58.9	48.9	17.1	11.5	Pass	



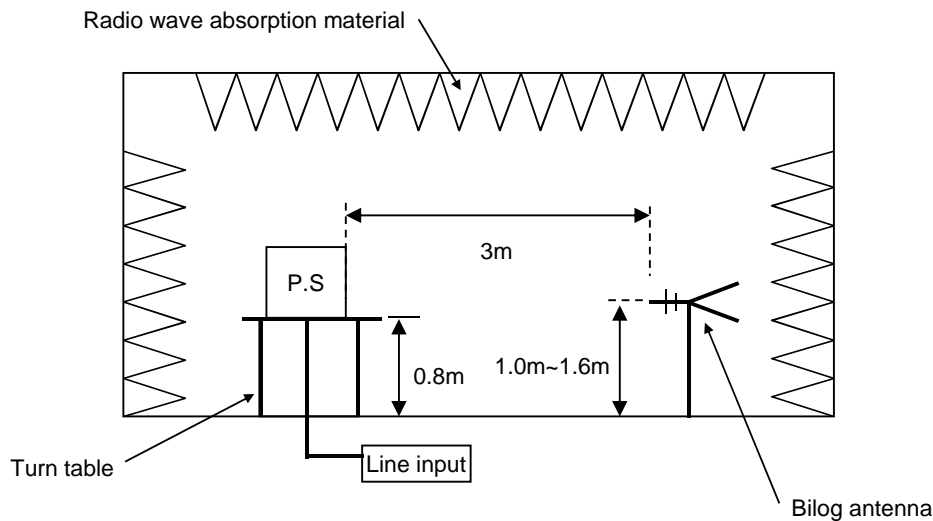
Frequency MHz	Polarization	Stability	Reading dB(μV)		Factor dB(1/m)	Level dB(μV/m)		Limit dB(μV/m)		Margin dB(μV/m)		Pass/Fail	Height cm	Angle deg	Remark
			QP	AV		QP	AV	QP	AV	QP	AV				
34.237	V	Stable	40.3		-9.8	30.5		40.0		9.5		Pass	105	66	
53.381	V	Stable	52.8		-20.5	32.3		40.0		7.7		Pass	105	359	

DATA SHEET		Date	13-Sep-17
Model	Circuit used for measurement	Temp.	25 degreeC
Test	EMI Line conduction & Radiated emission	Humid.	40 %RH
		Tested by	T.Sakuma

1. Line conduction



2. Radiated emission



Conditions

Test: EMI

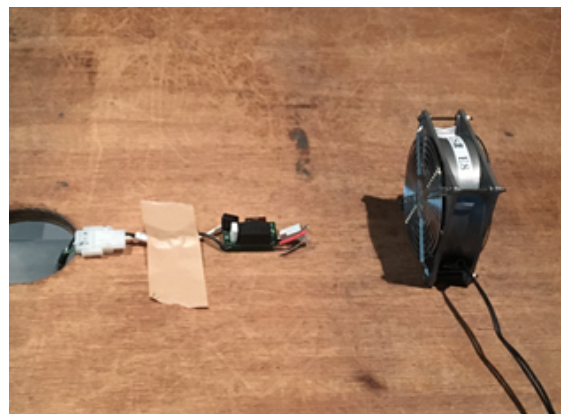
Model Name: TUHS3F15

○ Photographs of Test Set-Up

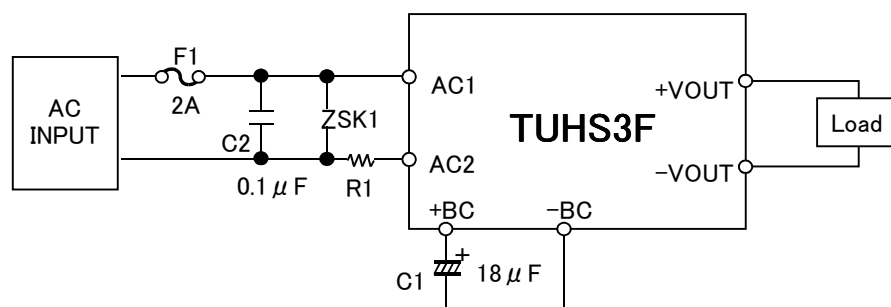
LINE CONDUCTION



RADIATED EMISSION



○ Test circuit



F1: SLT250V2A (Nippon Seisen)

R1: 1K100JA (TAMURA THERMAL DEVICE)

SK1: TND10V-511K (NIPPON CHEMI-CON)

2A

10 Ω

Fig.1 Testing circuitry